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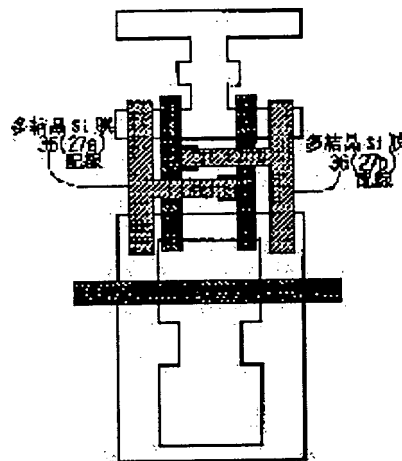
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To enable the wiring density to be lowered by a memory cell of a SRAM by providing the first and second cells with the wiring formed of the same semiconductor layer following the second layer.

SOLUTION: The wirings 27a, 27b for intersection coupling are formed of polycrystalline Si film 36 in the same layer as the polycrystalline Si layer used for the formation of the electrode, etc., of capacitance element in the memory cell of a DRAM to be the polycrystalline Si film after the second layer on an Si substrate. Next, the polycrystalline Si film 36, etc., are covered with an interlayer insulating film. In the memory cell of SRAM in ASIC, the wirings 27a, 27b for intersection coupling are formed of the polycrystalline Si film 36 in the same layer as that of the polycrystalline Si film for the formation of the electrode, etc., of capacity in the memory cell of a DRAM. Accordingly, in comparison with the memory cell of SRAM in the ASIC forming the wirings 27a, 27b of Al films, the density of the Al film wiring is lower than that of the memory cell so that the wirings 27a, 27b may be hardly affected by pattern deformation, or raising dust in the wiring formation step.



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